
Contents

List of Figures	i
List of Tables	iv
1 Introduction	1
1.1 History	1
1.2 Elemental and Compound Semiconductors.....	2
1.3 Development of III-Nitrides	4
1.4 Basic Material Properties	5
1.5 Technological Applications.....	7
1.5.1 Optical Devices Based on III-Nitrides.....	7
1.5.2 Electronic Devices Based on III-Nitrides	9
1.6 Objectives of this work.....	11
2 Theoretical background	13
2.1 Crystal Structure.....	13
2.2 Atomic Bond Properties	15
2.3 Band Structure	16
2.3.1 Temperature Dependence	18
2.3.2 Pressure Dependence	18
2.4 Defects.....	19
2.4.1 Structural Defects	19
2.4.2 Point Defects.....	20
2.4.3 Thermodynamics of Defect Formation.....	21
2.4.4 Fermi Level in Equilibrium	23
2.4.5 Formation Energy of Charged Defects	23
3 Experimental Methods	26
3.1 Growth of III-Nitrides	26
3.1.1 AlN PVT	27

3.1.2	MBE.....	27
3.1.3	MOCVD.....	28
3.2	MOCVD Reactor System.....	28
3.2.1	Illumination System.....	30
3.3	Illumination Efficiency Considerations.....	32
3.4	Electrical Characterization	35
3.4.1	I-V Measurements.....	36
3.4.2	Hall Effect Measurements	36
3.4.3	Electrical Contacts	38
3.5	Optical Characterization.....	39
3.5.1	Photoluminescence Spectroscopy.....	40
3.5.2	Transmission Spectroscopy	41
3.6	Other Characterization Techniques	41
3.6.1	SEM	41
3.6.2	AFM.....	43
3.6.3	XRD	44
3.6.4	SIMS	44
4	Conventional Point Defect Reduction in GaN	46
4.1	Power electronic applications.....	46
4.2	Carbon in gallium nitride.....	50
4.3	Supersaturation	51
4.4	Growth of GaN films.....	52
4.4.1	Carbon Incorporation into GaN	54
4.4.2	Electronic Properties of GaN.....	61
4.4.3	Creation of high μ GaN epitaxial films	67
5	Defect Quasi Fermi Level Control in n-GaN and AlGaN	75
5.1	Formation Energy of Point Defects.....	76
5.2	Application of Defect Quasi Fermi Level Control during Growth	78

5.3	Intensity Dependence	80
5.4	Defect Quasi Fermi Level control of C_N in the low concentration regime	87
5.5	Spatial control of defects	91
5.5.1	Comparison of above and below bandgap laser illumination in AlGaN	94
6	Defect Quasi Fermi Level Control of Mg-Migration in GaN.....	97
6.1	Significance of Mg for III-nitride devices.....	97
6.1.1	Significance of Mg memory effect for the development of power devices.....	98
6.2	Review of Mg memory effect.....	100
6.3	Growth and Illumination Experiments	102
6.4	Control of Mg migration by Defect Quasi Fermi level control.....	105
6.5	Creation of insulation layers.....	109
7	Conclusions and Future Work.....	113
7.1	Summary and Conclusions	113
7.1.1	Optimization of Conventional Point Defect Reduction.....	113
7.1.2	Defect Quasi Fermi Level Control in n-type GaN and AlGaN	113
7.1.3	Defect Quasi Fermi Level Control of Mg Migration in GaN	114
7.2	Future Work.....	115
8	References	117
9	Publications.....	125
	Acknowledgments	131